

吴正龙 北京 北京师范大学分析测试中心 100875

摘要: 通过改变XPS探测掠角,对硅表面的氧化层和富锗氧化硅表层薄膜样品进行非破坏性深度剖析测量,得到了有意义的结果。本文详细介绍了这一原理,并对这一分析方法的深度分辨等进行了讨论,为进行其它类型的薄膜XPS深度剖析测试提供了借鉴。

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An XPS Non-destructive Depth Profiling Methods Applied in the Study of Thin Films

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Abstract: The surfaces of silica on silicon and germanium-rich silica studied by one of the non-destructive depth profilings, take-off angle dependent XPS. The measurement theory is introduced in detail and its ability of the depth resolving is discussed. This measurement can also be applied in the study of other thin films.

Key words:

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